PSMN5R5-60YS



N-channel LFPAK 60 V, 5.2 m Ω standard level FET

Rev. 02 — 24 December 2009

Product data sheet

1. Product profile

1.1 General description

Standard level N-channel MOSFET in LFPAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- Advanced TrenchMOS provides low RDSon and low gate charge
- High efficiency in switching power converters
- Improved mechanical and thermal characteristics
- LFPAK provides maximum power density in a Power SO8 package

1.3 Applications

- DC-to-DC converters
- Lithium-ion battery protection
- Load switching

- Motor control
- Server power supplies

1.4 Quick reference data

Table 1. Quick reference

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$		-	-	60	V
I_D	drain current	T _{mb} = 25 °C; see <u>Figure 1</u>	<u>[1]</u>	-	-	100	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	130	W
Tj	junction temperature			-55	-	175	°C
Avalanci	he ruggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 100 A; V_{sup} ≤ 60 V; R_{GS} = 50 Ω; unclamped		-	-	170	mJ
Dynamic	characteristics						
Q_{GD}	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 75 \text{ A};$		-	11.2	-	nC
Q _{G(tot)}	total gate charge	$V_{DS} = 30 \text{ V}$; see Figure 14 and 15		-	56	-	nC



N-channel LFPAK 60 V, 5.2 m Ω standard level FET

Table 1. Quick reference ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static ch	naracteristics					
03011	drain-source on-state resistance	$V_{GS} = 10 \text{ V; } I_D = 15 \text{ A;}$ $T_j = 100 \text{ °C; see } \frac{\text{Figure 12}}{\text{ or } 12}$	-	-	8.3	mΩ
		$V_{GS} = 10 \text{ V; } I_D = 15 \text{ A;}$ $T_j = 25 \text{ °C; see } \frac{\text{Figure } 13}{\text{ Figure } 13}$	-	3.6	5.2	mΩ

^[1] Continuous current is limited by package.

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		
2	S	source	mb	D
3	S	source		
4	G	gate	9	4
mb	D	mounting base; connected to drain	1 2 3 4	mbb076 S
			SOT669 (LFPAK)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN5R5-60YS	LFPAK	plastic single-ended surface-mounted package (LFPAK); 4 leads	SOT669

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	60	V
V_{DGR}	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$		-	60	V
V_{GS}	gate-source voltage			-20	20	V
I_D	drain current	T _{mb} = 100 °C; see <u>Figure 1</u>		-	74	Α
		T _{mb} = 25 °C; see <u>Figure 1</u>	[1]	-	100	Α
I _{DM}	peak drain current	$t_p \le 10 \ \mu s$; pulsed; $T_{mb} = 25 \ ^{\circ}C$; see Figure 3		-	418	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	130	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
$T_{sld(M)}$	peak soldering temperature			-	260	°C
Source-dr	ain diode					
I _S	source current	$T_{mb} = 25 ^{\circ}C;$	<u>[1]</u>	-	100	Α
I _{SM}	peak source current	t _p ≤ 10 μs; pulsed; T _{mb} = 25 °C		-	418	Α
Avalanche	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 100 A; V_{sup} ≤ 60 V; R_{GS} = 50 Ω; unclamped		-	170	mJ

[1] Continuous current is limited by package.

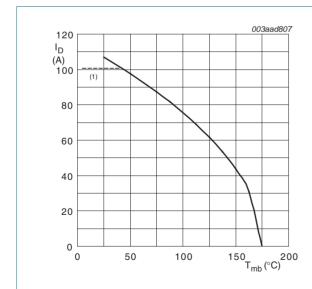
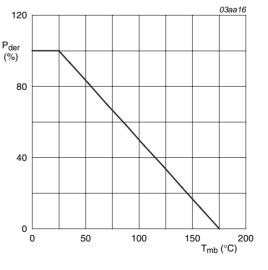


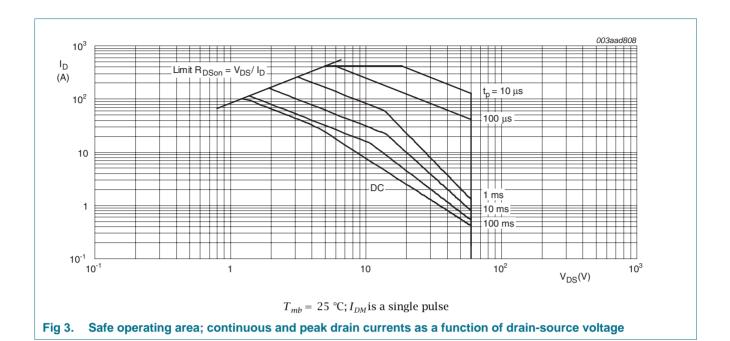
Fig 1. Continuous drain current as a function of mounting base temperature

 $V_{GS} \ge 10 \text{ V}$; (1) capped at 100 A due to package



 $P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$

Fig 2. Normalized total power dissipation as a function of mounting base temperature



5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j\text{-}mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	0.5	1.1	K/W

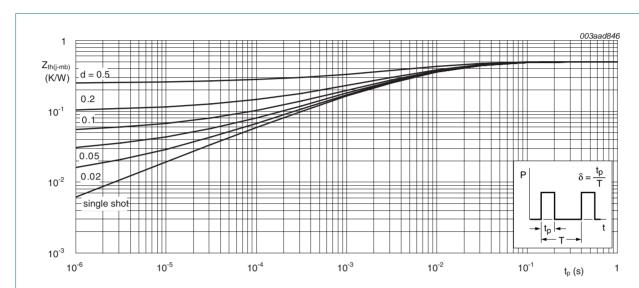


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration; typical values

6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V _{(BR)DSS} drain-source		$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^{\circ}C$	54	-	-	V
	breakdown voltage	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$	60	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; see <u>Figure 10</u> and <u>11</u>	2	3	4	V
V_{GSth}		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = -55$ °C; see Figure 11	-	-	4.6	V
		I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 175 °C; see <u>Figure 11</u>	0.95	-	-	V
I _{DSS}	drain leakage current	$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	5	μΑ
		$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ °C}$	-	-	100	μΑ
I _{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
R_{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 175 ^{\circ}\text{C};$ see Figure 12	-	7.6	12	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 100 \text{ °C};$ see Figure 12	-	-	8.3	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see Figure 13	-	3.6	5.2	mΩ
R_{G}	gate resistance	f = 1 MHz	-	0.7	-	Ω
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 75 \text{ A}; V_{DS} = 30 \text{ V}; V_{GS} = 10 \text{ V};$ see <u>Figure 14</u> and <u>15</u>	-	56	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	47.5	-	nC
Q_{GS}	gate-source charge	$I_D = 75 \text{ A}; V_{DS} = 30 \text{ V}; V_{GS} = 10 \text{ V};$ see <u>Figure 14</u> and <u>15</u>	-	18.7	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	$I_D = 75 \text{ A}$; $V_{DS} = 30 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 14	-	10.3	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	8.4	-	nC
Q_{GD}	gate-drain charge	$I_D = 75 \text{ A}; V_{DS} = 30 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 14 and 15	-	11.2	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	$V_{DS} = 30 \text{ V}$; see <u>Figure 14</u> and <u>15</u>	-	4.9	-	V
C _{iss}	input capacitance	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}; T_j = 25 °C;$	-	3501	-	pF
Coss	output capacitance	see Figure 16	-	457	-	pF
C _{rss}	reverse transfer capacitance		-	240	-	pF
d(on)	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 0.4 \Omega; V_{GS} = 10 \text{ V};$	-	23	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \Omega$	-	24	-	ns
t _{d(off)}	turn-off delay time		-	44	-	ns
t _f	fall time		-	14	-	ns

Table 6. Characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-dr	ain diode					
V _{SD}	source-drain voltage	$I_S = 15 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_j = 25 \text{ °C}$; see <u>Figure 17</u>	-	8.0	1.2	V
t _{rr}	reverse recovery time	$I_S = 25 \text{ A}$; $dI_S/dt = -100 \text{ A/}\mu\text{s}$; $V_{GS} = 0 \text{ V}$;	-	43	-	ns
Q _r	recovered charge	$V_{DS} = 30 \text{ V}$	-	58	-	nC

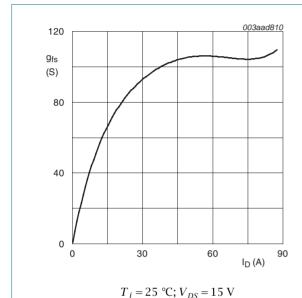
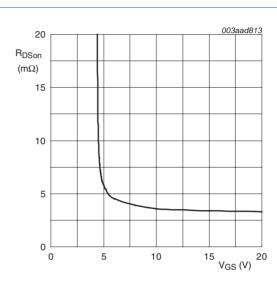


Fig 5. Forward transconductance as a function of drain current; typical values



 $T_i = 25$ °C; $I_D = 25$ A

Fig 6. Drain-source on-state resistance as a function of gate-source voltage; typical values

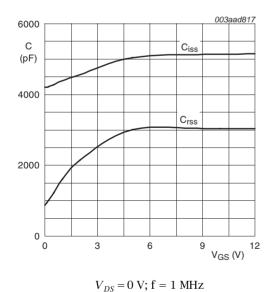


Fig 7. Input and reverse transfer capacitances as a function of gate-source voltage, typical values

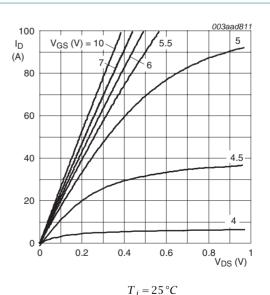


Fig 8. Output characteristics: drain current as a function of drain-source voltage; typical values

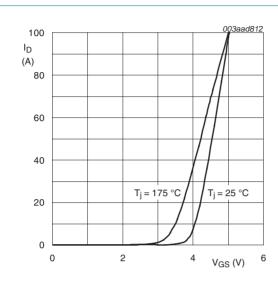
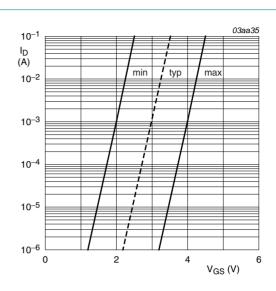


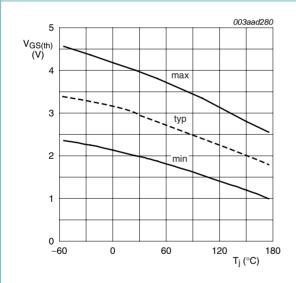
Fig 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values

 $V_{DS} > I_D \times R_{DSon}$



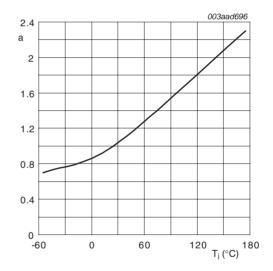
 $T_j=25\,^{\circ}C; V_{DS}=5V$

Fig 10. Sub-threshold drain current as a function of gate-source voltage



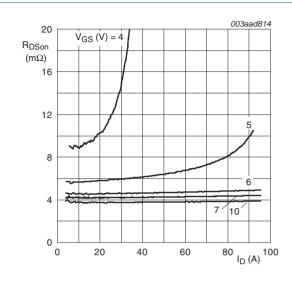
 $I_D = 1 \, mA; V_{DS} = V_{GS}$

Fig 11. Gate-source threshold voltage as a function of junction temperature



$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature.

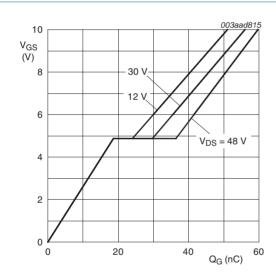


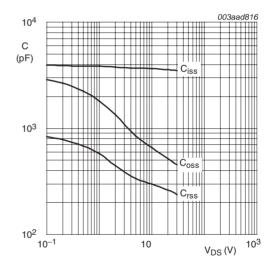
V_{GS}(pl)
V_{GS}(th)
V_{GS}
Q_{GS1} Q_{GS2}
Q_{GS} Q_G(tot)
003aaa508

Fig 13. Drain-source on-state resistance as a function of drain current; typical values

 $T_j = 25 \,^{\circ}C$

Fig 14. Gate charge waveform definitions





 $T_J = 25$ °C; $I_D = 75$ A

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

 $V_{GS} = 0 \text{ V; } f = 1 \text{ MHz}$

Fig 15. Gate-source voltage as a function of gate charge; typical values

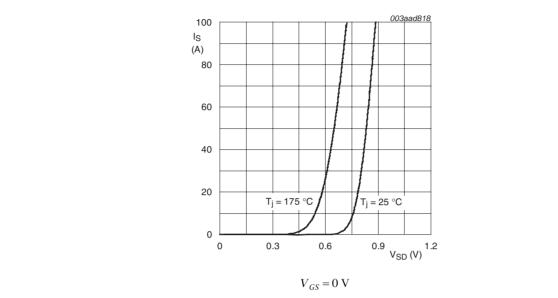


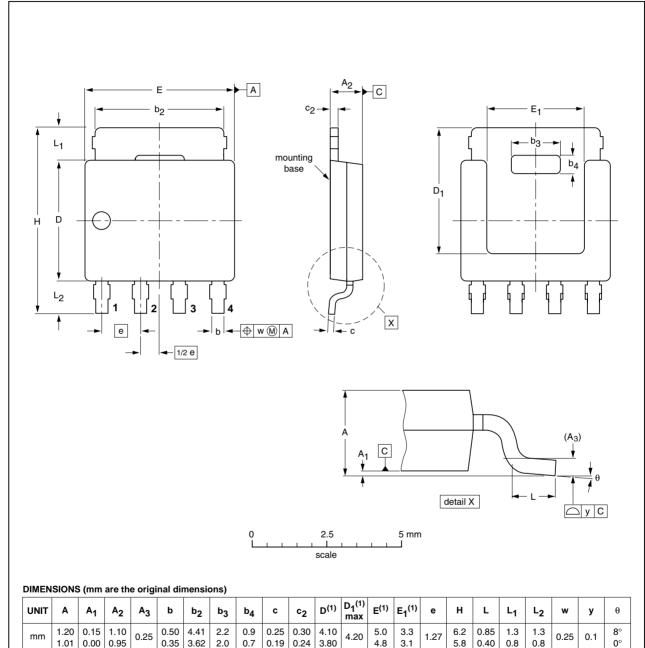
Fig 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

10 of 15

7. Package outline

Plastic single-ended surface-mounted package (LFPAK); 4 leads

SOT669



1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT669		MO-235				04-10-13 06-03-16

Fig 18. Package outline SOT669 (LFPAK)

N-channel LFPAK 60 V, 5.2 m Ω standard level FET

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN5R5-60YS_2	20091224	Product data sheet	-	PSMN5R5-60YS_1
Modifications:	 Status cha 	anged from objective to pro	oduct.	
PSMN5R5-60YS_1	20091201	Objective data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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For sales office addresses, please send an email to:salesaddresses@nexperia.com

PSMN5R5-60YS

N-channel LFPAK 60 V, 5.2 m Ω standard level FET

11. Contents

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